

SMD SILICON PHOTO DIODES

BL-LS3528A0S1PD

Features:

- 3.5mmx2.8mm SMD, 1.9mm THICKNESS PLCC2 package, SILICON PHOTO DIODES
- Choice of various viewing angles.
- Diffused and Water clear lens are available.
- Fast response time.
- High photo sensitivity.
- Small junction capacitance.
- The epoxy package itself is an IR filter, spectrally matched to GaAs or GaAlAs IR emitter.
- PACKAGE: 2KPCS/REEL.
- RoHs Compliance



Applications:

- High speed photo detector
- Camera
- Infrared remote controller for TVs VCR, audio equipment, air conditioner, etc.

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Rating	Unit
Power Dissipation	P_d	160	mW
Reverse Voltage	V_R	35	V
Operation Temperature	T_{OPR}	-40 to +100	°C
Storage Temperature	T_{STG}	-40 to +100	°C
Lead Soldering Temperature	TSOL	Max.260±5 °C for 3 sec Max. (1.6mm from the base of the epoxy bulb)	°C

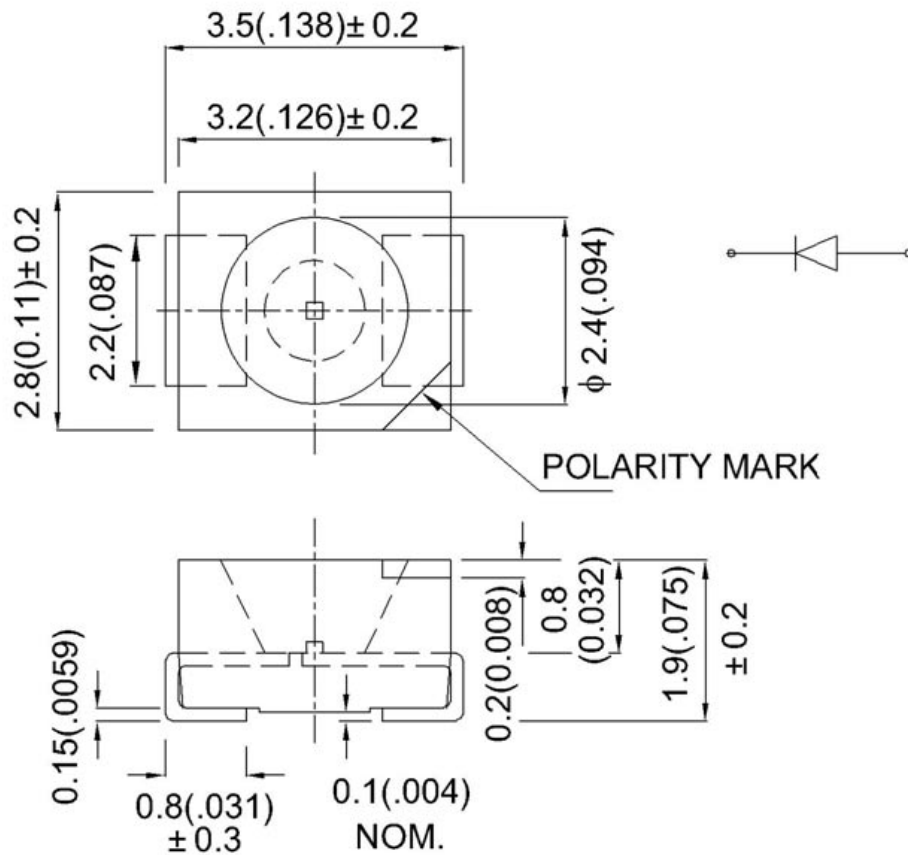
Electronic Optical Characteristics at Ta=25°C

Items	Symbol	Min.	Typ.	Max.	Unit	Condition
Wavelength of Peak Sensitivity	λ_p	-	900	-	nm	-
Open Circuit Voltage	V_{OC}	-	0.40	-	V	H=5mW/cm ² $\lambda_p=900\text{nm}$
Short Circuit Current	I_{SC}	-	2	-	uA	
Reverse Light Current	I_L	-	3.5	-	uA	H=5mW/cm ² $\lambda_p=900\text{nm}$ $V_R=5\text{V}$
Reverse Dark Current	I_D	-	-	10	nA	H=0mW/cm ² $V_R=10\text{V}$
Reverse Break down Voltage	V_{BR}	35	170	-	V	H=0mW/cm ² $I_R=100\text{uA}$
Viewing angle	$2\theta_{1/2}$	-	120	-	Deg	
Rise/Fall Time	T_r/T_f	-	6/6	-	nS	$R_L=10000$ $V_R=10\text{V}$

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■ **Package configuration & Internal circuit diagram**



Notes:

1. All dimensions are in millimeters (inches)
2. Tolerance is $\pm 0.25(0.01)$ unless otherwise noted.
3. Specifications are subject to change without notice.

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■ Packing and weighting

